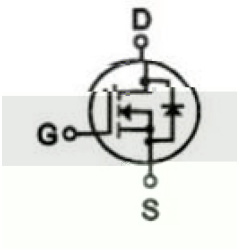
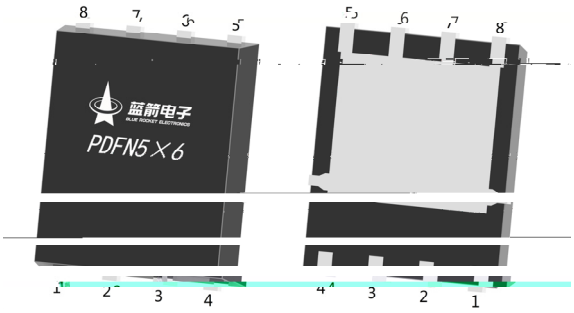
PDFN5×6 Ł N ڜ ٦
N-Channel MOSFET in a PDFN5×6 Plastic Package .

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ڂ ، ļ ψ
Low $R_{DS(ON)}$ to minimize conductive loss;low Gate Charge for fast switching;Low Thermal resistance; Qualified to AEC-Q101 Standards for High Reliability; HF Product.

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Battery Management, Meet the stringent requirements of automotive applications.

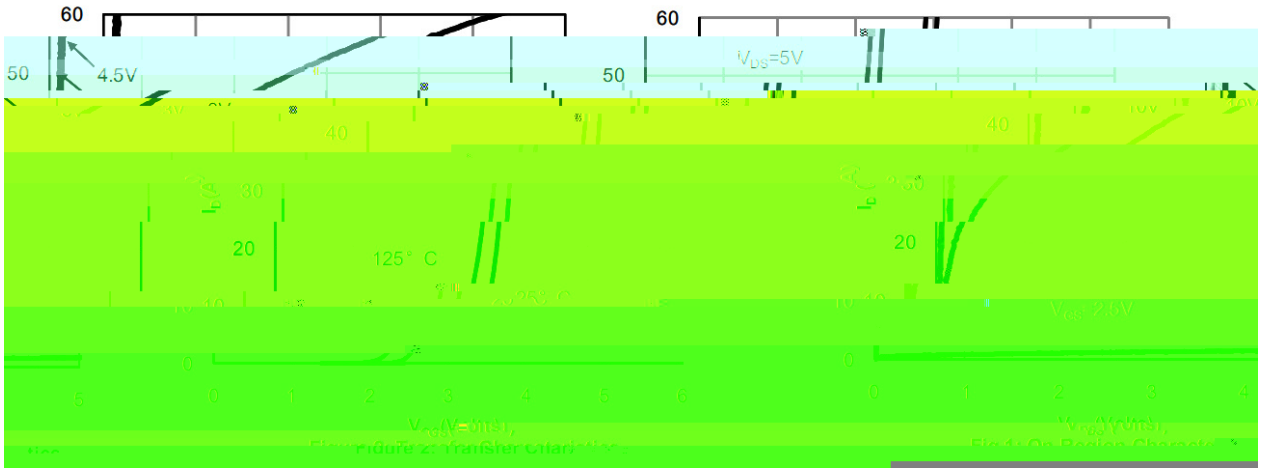




PIN1 2 3 S PIN4 G PIN5 6 7 8 D

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See Marking Instructions.

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	40	V
Drain Current - Continuous	I_D	170	A
Drain Current – Pulsed	I_{DM}	340	A
Gate-Source Voltage	V_{GS}	± 20	V
Power Dissipation	$P_D(T_c=25$)	65	W
Single Pulse Avalanche Energy(L=0.5mH)	E_{AS}	358	mJ
Avalanche Current(L=0.5mH)	I_{AS}	32	A
Junction and Storage Temperature Range	T_j, T_{stg}	-55 to 150	
Thermal resistance, junction - case	$R_{\theta JC}$	1.9	/ W
Thermal resistance, junction - ambient	$R_{\theta JA}$GS		



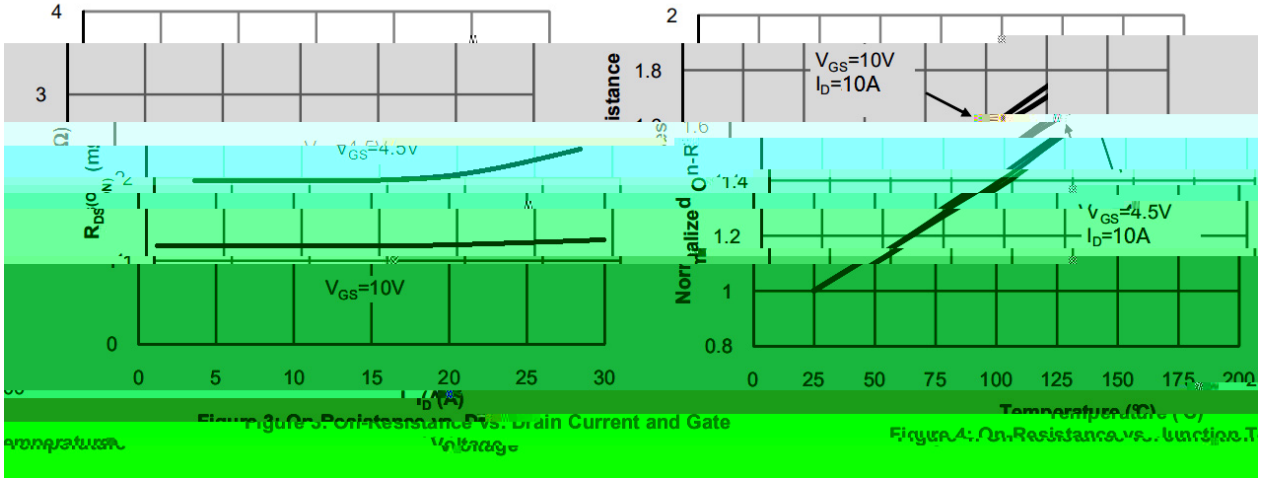
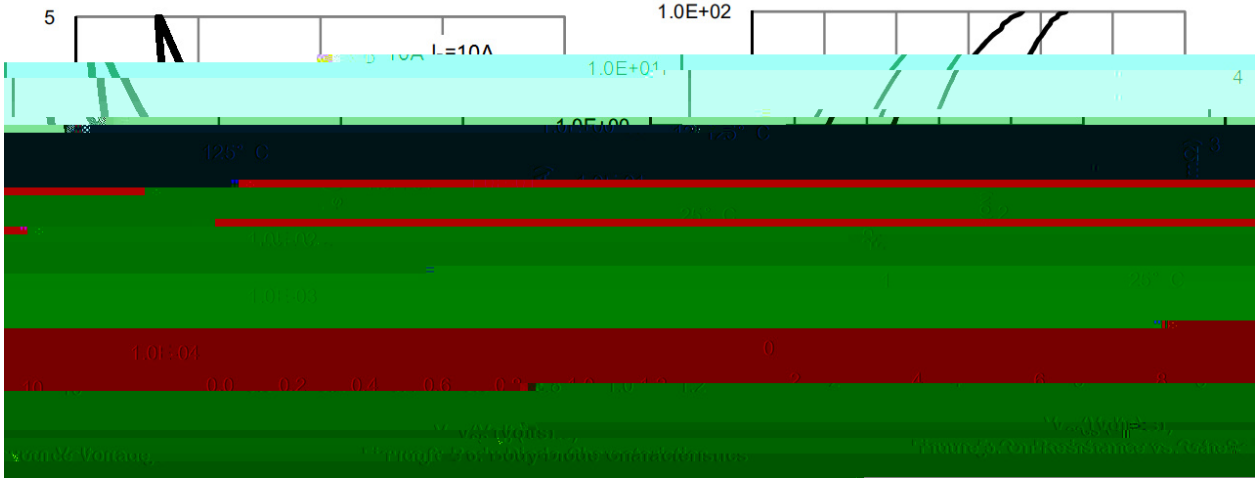
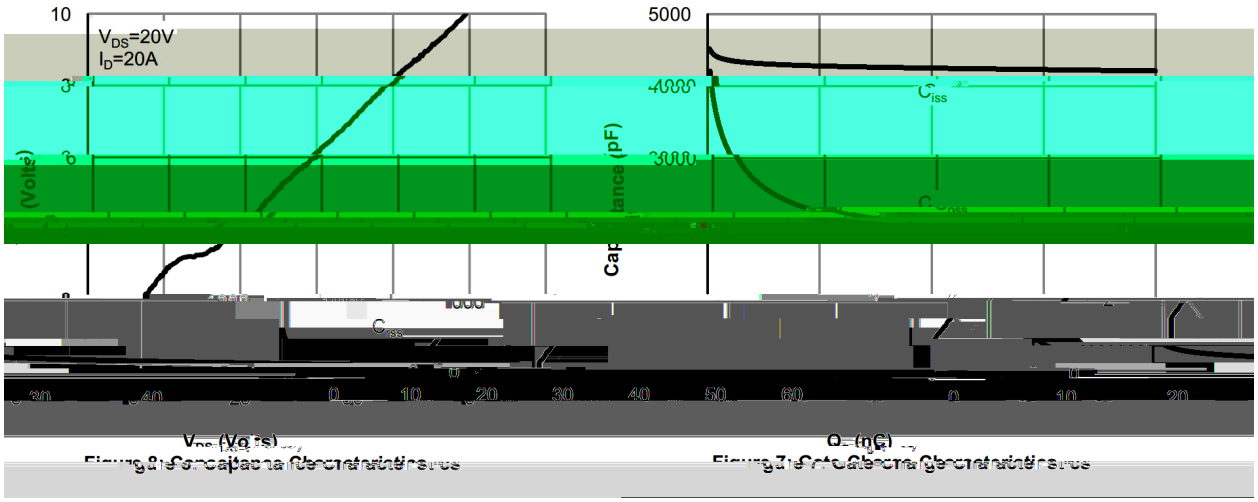
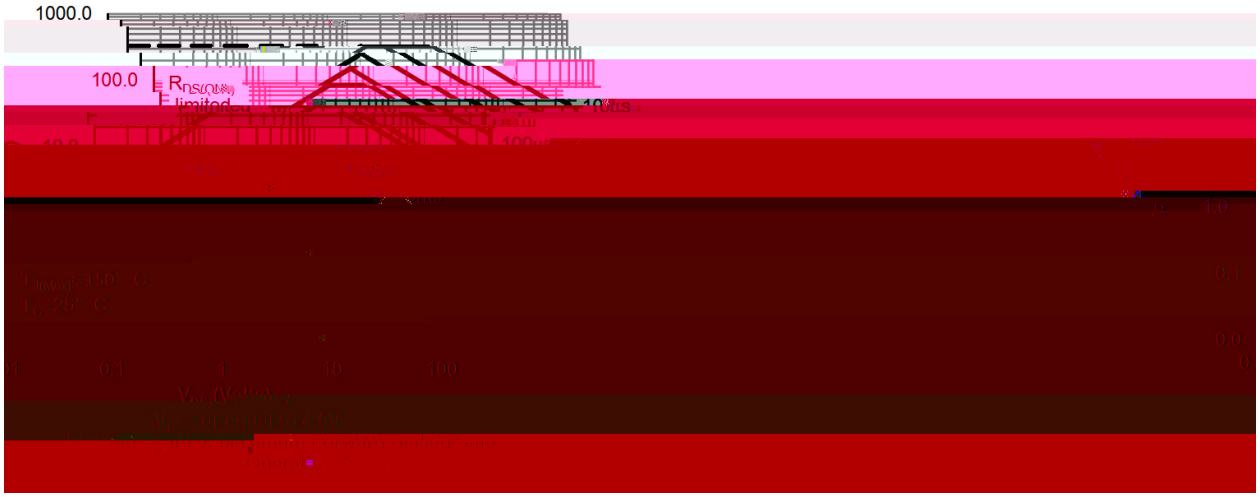


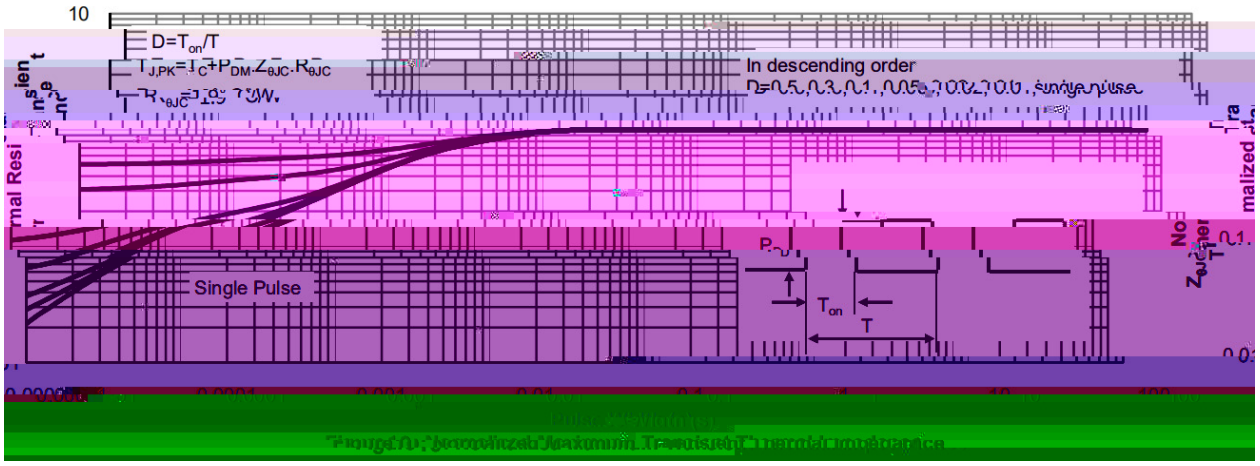
Figure 3 On-Resistance vs. Drain Current and Gate Voltage

Figure 4: On-Resistance vs. Junction Temperature




10
V_{DS}=20V
I_D=20A
(Volts)
5000
C_{iss}
Capacitance (pF)
C_{oss}
C_{rss}
V_{DS} (Volts)
Q_g (nC)


1000.0
100.0
$R_{DS(ON)}$ limited
10μs
100μs
1ms
10ms
100ms
1s
10s
DC
$T_{J(max)}$=150° C
T_C=25° C
0.1
1
10
100
V_{DS} (Volts)
V_{GS} equal to 10V
Single Pulse


10
D=T_{on}/T
$T_{J,PK}$=T_C+P_{DM}·$Z_{\theta JC}$·$R_{\theta JC}$
$R_{\theta JC}$=1.5 °C/W
In descending order
D=0.5, 0.3, 0.1, 0.05, 0.02, 0.01, Single Pulse
Single Pulse
P_{DM}
T_{on}
T
0.1
0.01

Rev.B Feb.-2023



Note χ	
BR χ	Company Code
Q:	Automobile halogen-free product Code
015N04S χ	Product Type
****:	Lot No. Code, code change with Lot No

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1	أ ♬ □ 150 200 ژ 60 120sec;	1.Preheating:150~200 , Time:60~120sec.
2	□ 255±5 ژ ٨ 5±0.5sec;	2.Peak Temp.:255±5 , Duration:5±0.5sec.
3	١ ھ 2 10 /sec.	3. Cooling Speed: 2~10 /sec.

□ χ 260±5 ژ χ 10±

Note: